

Oral Presentation

## [AMD7]Oxide TFT: Fabrication Process

Chair: Toshiaki Arai (JOLED Inc.)

Co-Chair: Yujiro Takeda (Sharp)

Fri. Nov 29, 2019 1:20 PM - 2:40 PM Mid-sized Hall B (1F)

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2:05 PM - 2:25 PM

## [AMD7-3]Highly Stable High Mobility Top-gate Structured Oxide TFT by Supplying Optimized Oxygen and Hydrogen to Semiconductors

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Keywords:High mobility, Stability, Top-gate structure, oxide TFTs

Top-gate self-aligned structured TFT is appropriate for the high-end display. However, it is hard to realize highly stable high mobility characteristics, because GI deposition affects active surface in top-gate structure. Here we realize highly stable high mobility oxide TFTs by using thermal-ALD and oxygen sourcing plasma treatment for GI process.